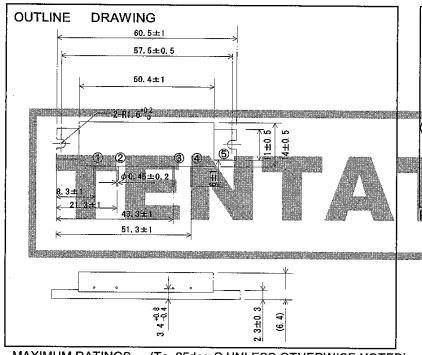
ATTENTION
OBSERVE PRECAUTIONS
FOR HANDLING
ELETROSTATIC
SENSITIVE
DEVICES

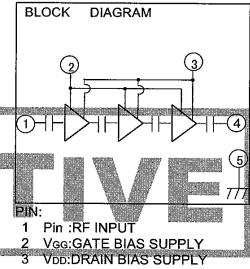
Revision date: 27th/June. '02

MITSUBISHI RF POWER MODULE

RA13H8891MB

Silicon MOS FET Power Amplifier, 890-915MHz 13W MOBILE RADIO





Po:RFOUTPUT

GND:FIN

MAXIMUM RATINGS (Tc=25deg.C UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	CONDITIONS	RATINGS	UNIT
VDD	SUPPLY VOLTAGE	VGG<5V,Zg=Zl=50ohm	17	V
Vgg	GATE BIAS VOLTAGE	VDD<12.5V,Pin=50mW,Zg=ZI=50ohm	6	V
Pin	INPUT POWER	f=890-915MHz,Zg=Zl=50ohm	5	mW
Po	OUTPUT POWER	f=890-915MHz,Zg=ZI=50ohm	20	W
Tc(OP)	OPERATION CASE TEMPERATURE	f=890-915MHz,Zg=Zl=50ohm	-30 to +110	deg.C
Tstg	STORAGE TEMPERATURE		-40 to +110	deg.C

Note: Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (Tc=25deg.C,Zg=ZI=50ohm UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	ĺ
f	FREQUENCY RANGE		890		915	MHz
Po	OUTPUT POWER	Vdd=12.5V, Vgg=5V, Pin=1mW	13			W
Et	TOTAL EFFICIENCY		35			%
2fo	2nd HARMONIC				-30	dBc
	INPUT VSWR				3:1	-
		Zg=50ohm, Vdd=10 - 16V, LOAD VSWR = 3:1, Pin=0.5 –2mW, Po<20W(Vgg Control)	No parasitic oscillation			
		Vdd=15.2V, Pin=1mW, Po=13W(Vgg Control), Zg=50ohm, LOAD VSWR = 20:1	No degradation or destroy			-

ABOVE PARAMETERS, RATINGS, LIMITS AND CONDITIONS ARE SUBJECT TO CHANGE.

-Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.